

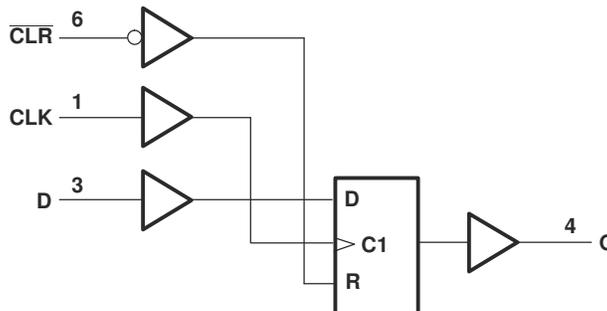
## SN54SC1G175-SEP Single D-Type Flip-Flop With Asynchronous Clear

### 1 Features

- VID V62/26610
- Radiation - Total Ionizing Dose (TID):
  - TID characterized up to 50krad(Si)
  - TID performance assurance up to 30krad(Si)
  - Radiation Lot Acceptance Testing (RLAT) for every wafer lot up to 30krad(Si)
- Radiation - Single-Event Effects (SEE):
  - Single Event Latch-Up (SEL) immune up to 50MeV-cm<sup>2</sup>/mg at 125°C
  - Single Event Transient (SET) characterized up to LET = 50MeV-cm<sup>2</sup>/mg
- Wide operating range of 1.2V to 5.5V
- 5.5V tolerant input pins
- Supports standard pinouts
- Up to 150Mbps with 5V or 3.3V V<sub>CC</sub>
- Latch-up performance exceeds 100mA per JESD 78
- Space enhanced plastic:
  - Supports Defense and Aerospace Applications
  - Controlled baseline
  - Au bondwire and NiPdAu lead finish
  - Meets NASA ASTM E595 outgassing specification
  - One fabrication, assembly, and test site
  - Extended product life cycle
  - Product traceability

### 2 Applications

- [Enable or disable a digital signal](#)
- [Controlling an indicator LED](#)



Logic Diagram

### 3 Description

The SN54SC1G175-SEP device is a single D-type flip-flop with asynchronous clear (CLR) input. When CLR is HIGH, data from the input pin (D) transfers to the output pin (Q) on the clock's (CLK) rising edge. When CLR is LOW, the Q is forced into the LOW state, regardless of the clock edge or data on D.

#### Package Information

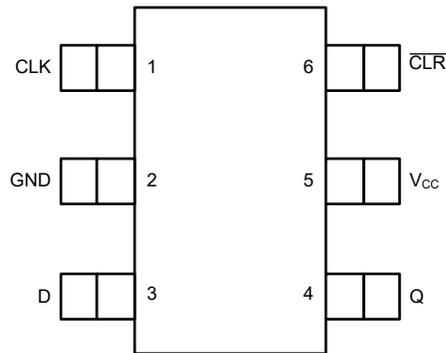
PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>	BODY SIZE <sup>(3)</sup>
SN54SC1G175-SEP	DBV (SOT-23, 6)	2.9mm × 2.8mm	2.9mm × 1.6mm

- (1) For more information, see [Section 11](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.

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## 4 Pin Configuration and Functions



**Figure 4-1. DBV Package, 6-Pin SOT-23 (Top View)**

**Table 4-1. Pin Functions**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
CLK	1	I	Clock input
GND	2	G	Ground Pin
D	3	I	Data input
Q	4	O	Output
V <sub>CC</sub>	5	P	Positive supply
CLR	6	I	Asynchronous clear pin

(1) Signal Types: I = Input, O = Output, G = Ground, P = Power



over operating free-air temperature range (unless otherwise noted)

Specifications	Description	Condition	MIN	MAX	UNIT
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 1.65V		4	mA
		V <sub>CC</sub> = 2.3V		8	
		V <sub>CC</sub> = 3.0V		16	
				24	
	V <sub>CC</sub> = 4.5V		32		
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 1.2V to 5.0V		20	ns/V
		V <sub>CC</sub> = 1.8V ± 0.15V		20	
		V <sub>CC</sub> = 2.5V ± 0.2V		20	
		V <sub>CC</sub> = 3.3V ± 0.3V		10	
		V <sub>CC</sub> = 5.0V ± 0.5V		5	
T <sub>A</sub>	Operating free-air temperature		-55	125	°C

## 5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC <sup>(1)</sup>						UNIT
		R <sub>θJA</sub>	R <sub>θJC(top)</sub>	R <sub>θJB</sub>	Ψ <sub>JT</sub>	Ψ <sub>JB</sub>	R <sub>θJC(bot)</sub>	
DBV (SOT-23, 6)	6	329.6	244.7	217.7	142.1	216.7	-	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

## 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	-55°C to 125°C			UNIT
			MIN	TYP	MAX	
V <sub>OH</sub>	I <sub>OH</sub> = -100 μA	1.1V to 5.5V	V <sub>CC</sub> - 0.1			V
	I <sub>OH</sub> = -4mA	1.65V	1.2			
	I <sub>OH</sub> = -8mA	2.3V	1.9			
	I <sub>OH</sub> = -12mA	2.7V	2.2			
	I <sub>OH</sub> = -16mA	3V	2.4			
	I <sub>OH</sub> = -24mA	3V	2.3			
	I <sub>OH</sub> = -32mA	4.5V	3.8			
V <sub>OL</sub>	I <sub>OL</sub> = 100 μA	1.1V to 5.5V	0.15			V
	I <sub>OL</sub> = 4mA	1.65V	0.45			
	I <sub>OL</sub> = 8mA	2.3V	0.3			
	I <sub>OL</sub> = 12mA	2.7V	0.4			
	I <sub>OL</sub> = 16mA	3V	0.4			
	I <sub>OL</sub> = 24mA	3V	0.55			
	I <sub>OL</sub> = 32mA	4.5V	0.55			
I <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	V <sub>CC</sub> = 0V to 5.5 V	±5			μA
I <sub>OFF</sub>	V <sub>I</sub> or V <sub>O</sub> = V <sub>CC</sub>	V <sub>CC</sub> = 0V	±10			μA
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	V <sub>CC</sub> = 1.1V to 5.5 V	10			μA
ΔI <sub>CC</sub>	One input at V <sub>CC</sub> - 0.6V, other inputs at V <sub>CC</sub> or GND	3.0V to 5.5V	500			μA
C <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3V	3.5			pF
C <sub>O</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3V				pF

## 5.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V <sub>CC</sub>	-55°C to 125°C			UNIT
				MIN	TYP	MAX	
f <sub>clock</sub>	Clock frequency		1.2V ± 0.1V			12	MHz
			1.5V ± 0.12			63	
			1.8V ± 0.15V			83	
			2.5V ± 0.2V			79	
			3.3V ± 0.3V			88	
			5V ± 0.5V			92	
t <sub>w</sub>	Pulse duration	CLR low	1.2V ± 0.1V	8			ns
			1.5V ± 0.12V	8			
			1.8V ± 0.15V	8			
			2.5 ± 0.2V	8			
			3.3V ± 0.3V	8			
			5V ± 0.5V	8			
		CLK high or low	1.2V ± 0.1V	3			ns
			1.5V ± 0.12V	3			
			1.8V ± 0.15V	3			
			2.5 ± 0.2V	2			
			3.3V ± 0.3V	2			
			5V ± 0.5V	2			
t <sub>SU</sub>	Setup time before CLK↑	Data before CLK↑	1.2V ± 0.1V	25			ns
			1.5V ± 0.12V	14			
			1.8V ± 0.15V	9			
			2.5 ± 0.2V	6			
			3.3V ± 0.3V	6			
			5V ± 0.5V	6			
		CLR Inactive	1.2V ± 0.1V	23			ns
			1.5V ± 0.12V	7			
			1.8V ± 0.15V	5			
			2.5 ± 0.2V	6			
			3.3V ± 0.3V	5			
			5V ± 0.5V	4			
t <sub>H</sub>	Hold time	Data after CLK↑	1.2V ± 0.1V	0			ns
			1.5V ± 0.12V	0			
			1.8V ± 0.15V	0			
			2.5 ± 0.2V	0			
			3.3V ± 0.3V	0			
			5V ± 0.5V	0			

### 5.7 Switching Characteristics

over operating free-air temperature range; typical values measured at  $T_A = 25^\circ\text{C}$  (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	$V_{CC}$	-55°C to 125°C			UNIT				
					MIN	TYP	MAX					
$t_{pd}$	CLK	Q	$C_L = 15\text{pF}$	$1.2\text{V} \pm 0.1\text{V}$			112	ns				
				$1.5\text{V} \pm 0.12\text{V}$			26.4					
				$1.8\text{V} \pm 0.15\text{V}$			17.3					
				$2.5\text{V} \pm 0.2\text{V}$			9.7					
				$3.3\text{V} \pm 0.3\text{V}$			6.9					
				$5\text{V} \pm 0.5\text{V}$			4.9					
			$C_L = 30\text{pF}$	$1.8\text{V} \pm 0.15\text{V}$			17.8					
				$2.5\text{V} \pm 0.2\text{V}$			10					
			$C_L = 50\text{pF}$	$3.3\text{V} \pm 0.3\text{V}$			7.3					
				$5\text{V} \pm 0.5\text{V}$			5.4					
			$t_{pd}$	$\overline{\text{CLR}}$	Q	$C_L = 15\text{pF}$	$1.2\text{V} \pm 0.1\text{V}$				122	ns
							$1.5\text{V} \pm 0.12\text{V}$				26.7	
$1.8\text{V} \pm 0.15\text{V}$							18.4					
$2.5\text{V} \pm 0.2\text{V}$							10.2					
$3.3\text{V} \pm 0.3\text{V}$							7.2					
$5\text{V} \pm 0.5\text{V}$							4.7					
$C_L = 30\text{pF}$	$1.8\text{V} \pm 0.15\text{V}$						19					
	$2.5\text{V} \pm 0.2\text{V}$						10.5					
$C_L = 50\text{pF}$	$3.3\text{V} \pm 0.3\text{V}$						7.7					
	$5\text{V} \pm 0.5\text{V}$						5.3					

### 5.8 Typical Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise noted)

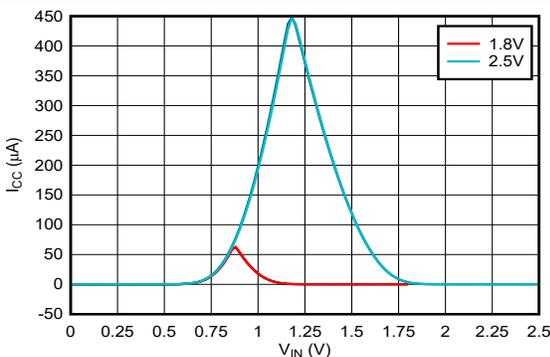


Figure 5-1. Supply Current Across Input Voltage 1.8V and 2.5V Supply

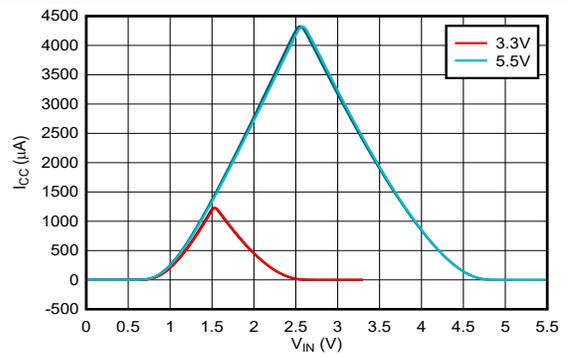


Figure 5-2. Supply Current Across Input Voltage 3.3V and 5.5V Supply

## 6 Parameter Measurement Information

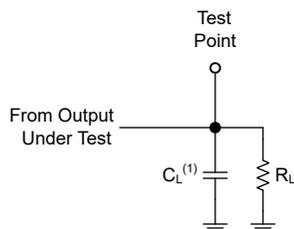
Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1MHz,  $Z_O = 50\Omega$ ,  $t_f \leq 2.5\text{ns}$ .

For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured individually with one input transition per measurement.

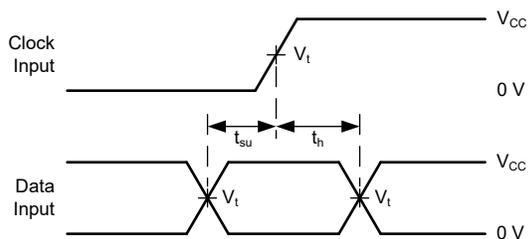
**Table 6-1. Push-Pull Outputs**

$V_{CC}$	$V_t$	$R_L$	$C_L$	$\Delta V$
$1.2\text{V} \pm 0.1\text{V}$	$V_{CC}/2$	$2\text{k}\Omega$	15pF	0.1V
$1.5\text{V} \pm 0.12\text{V}$	$V_{CC}/2$	$2\text{k}\Omega$	15pF	0.1V
$1.8\text{V} \pm 0.15\text{V}$	$V_{CC}/2$	$1\text{k}\Omega$	15pF/30pF	0.15V
$2.5\text{V} \pm 0.2\text{V}$	$V_{CC}/2$	$500\Omega$	15pF/30pF	0.15V
$3.3\text{V} \pm 0.3\text{V}$	1.5V	$500\Omega$	15pF/50pF	0.3V
$5.0\text{V} \pm 0.5\text{V}$	1.5V	$500\Omega$	15pF/50pF	0.3V

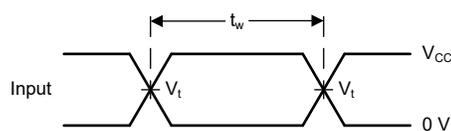


(1)  $C_L$  includes probe and test-fixture capacitance.

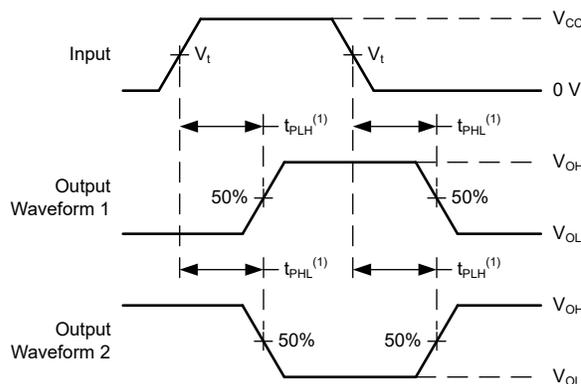
**Figure 6-1. Load Circuit for Push-Pull Outputs**



**Figure 6-3. Voltage Waveforms, Setup and Hold Times**

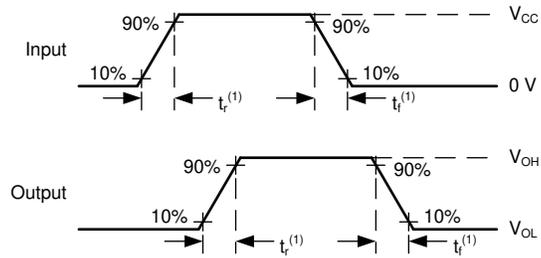


**Figure 6-2. Voltage Waveforms, Pulse Duration**



(1) The greater between  $t_{PLH}$  and  $t_{PHL}$  is the same as  $t_{pd}$ .

**Figure 6-4. Voltage Waveforms Propagation Delays**



(1) The greater between  $t_r$  and  $t_f$  is the same as  $t_t$ .

**Figure 6-5. Voltage Waveforms, Input and Output Transition Times**

## 7 Detailed Description

### 7.1 Overview

The SN54SC1G175-SEP device is a single D-type flip-flop with asynchronous clear ( $\overline{\text{CLR}}$ ) input. When  $\overline{\text{CLR}}$  is HIGH, data from the input pin (D) is transferred to the output pin (Q) on the clock's (CLK) rising edge. When  $\overline{\text{CLR}}$  is LOW, the Q is forced into the LOW state, regardless of the clock edge or data on D.

### 7.2 Functional Block Diagram

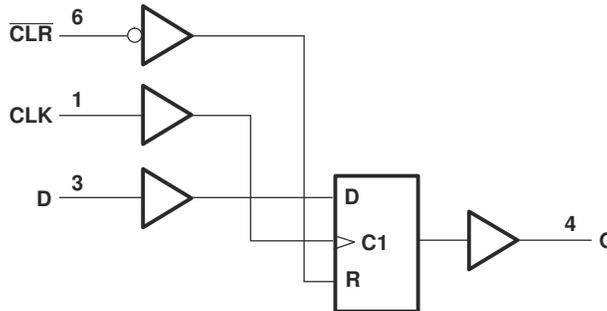


Figure 7-1. Logic Diagram (Positive Logic)

### 7.3 Feature Description

#### 7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

#### 7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ( $R = V \div I$ ).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

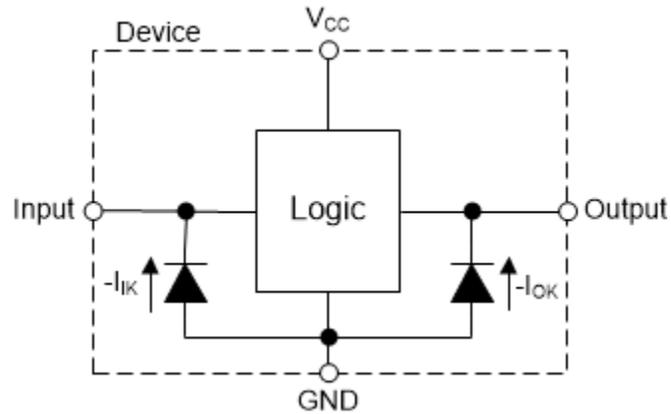
Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10k $\Omega$  resistor, however, is recommended and will typically meet all requirements.

#### 7.3.3 Clamp Diode Structure

Figure 7-2 shows the inputs and outputs to this device have negative clamping diodes only.

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



**Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output**

## 7.4 Device Functional Modes

Function Table lists the functional modes for SN54SC1G175-SEP.

**Table 7-1. Function Table**

INPUTS <sup>(1)</sup>			OUTPUT
CLR	CLK	D	Q <sup>(2)</sup>
H	↑	L	L
H	↑	H	H
H	H or L	X	Q <sub>0</sub>
L	X	X	L

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

## 8 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

Multiple SN54SC1G175-SEP devices can be used in tandem to create a shift register of arbitrary length. In this example, we use four SN54SC1G175-SEP devices to form a 4-bit serial shift register. By connecting all CLK inputs to a common clock pulse and tying each output of one device to the next, we can store and load 4-bit values on demand. We demonstrate loading the 4 bit value *1101* into memory by setting *Serial Input Data* to each desired memory bit, and by sending a clock pulse for each bit, we sequentially move all stored bits from left to right

(A → B → C → D)

### 8.2 Typical Application

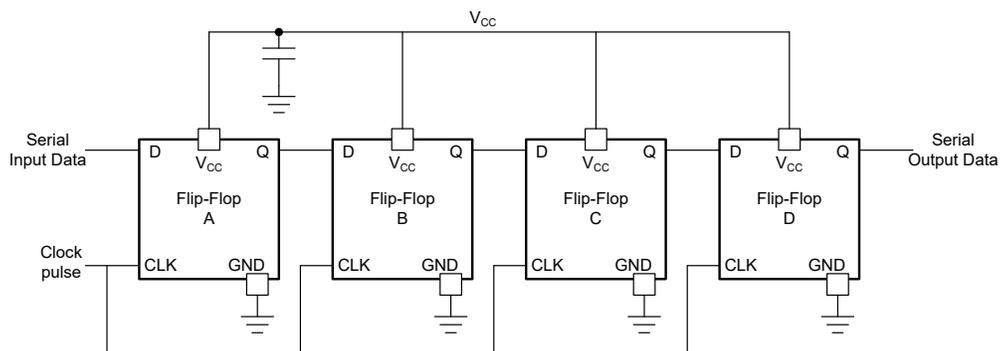


Figure 8-1. 4-Bit Serial Shift Register

### 8.2.1 Design Requirements

The SN54SC1G175-SEP device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits.

The SN54SC1G175-SEP allows switching control of analog and digital signals with a digital control signal. All input signals should remain as close to either 0V or  $V_{CC}$  as possible for optimal operation.

#### 8.2.1.1 Power Considerations

Ensure that the desired supply voltage is within the range specified in the *Electrical Characteristics*. The supply voltage sets the device electrical characteristics of the device, as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN54SC1G175-SEP plus the maximum static supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN54SC1G175-SEP plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN54SC1G175-SEP can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN54SC1G175-SEP can drive a load with total resistance described by  $R_L \geq V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in the [CMOS Power Consumption and Cpd Calculation application note](#).

Thermal increase can be calculated using the information provided in the [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#).

#### CAUTION

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 8.2.1.2 Input Considerations

Input signals must cross  $V_{IL(max)}$  to be considered a logic LOW, and  $V_{IH(min)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN54SC1G175-SEP (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10k $\Omega$  resistor value is often used due to these factors.

The SN54SC1G175-SEP has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Electrical Characteristics* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* for additional information regarding the inputs for this device.

### 8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

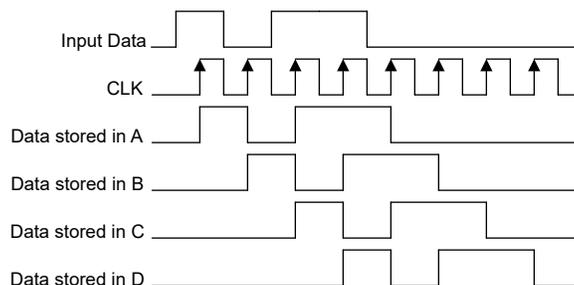
Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

### 8.2.2 Detailed Design Procedure

1. Recommended input conditions:
  - For rise time and fall time specifications, see  $\Delta t/\Delta v$  in the *Recommended Operating Conditions* table.
  - For specified high and low levels, see  $V_{IH}$  and  $V_{IL}$  in the *Recommended Operating Conditions* table.
  - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5V at any valid  $V_{CC}$ .
2. Recommended output conditions:
  - Load currents not exceeding  $\pm 50\text{mA}$ .
3. Frequency selection criterion:
  - The effects of frequency upon the device's power consumption should be studied in the [CMOS Power Consumption and CPD Calculation application note](#).
  - Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the *Layout* section.

### 8.2.3 Application Curves



**Figure 8-2. Application Timing Chart**

**Table 8-1. Stored Data Values**

Serial Input Data	Stored A	Stored B	Stored C	Stored D
1	0	0	0	0
0	1	0	0	0
1	0	1	0	0
1	1	0	1	0
0	1	1	0	1

### 8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

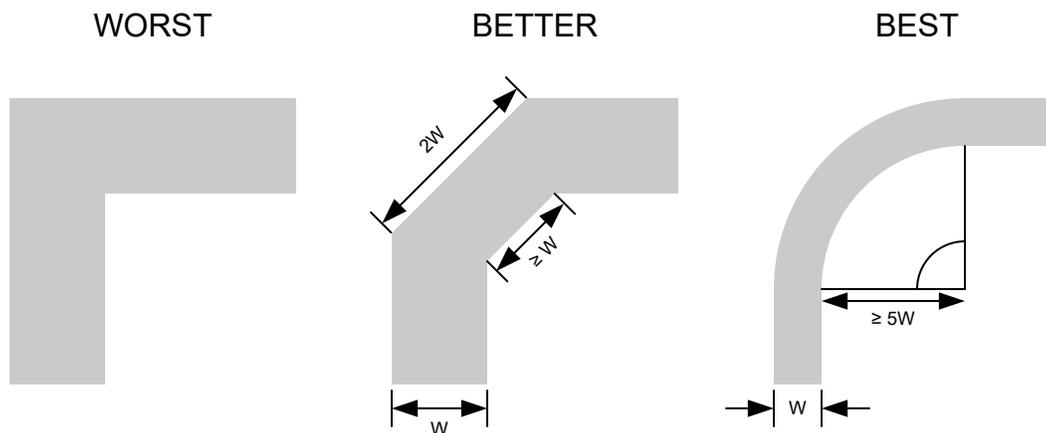
Verify that each  $V_{CC}$  terminal has a good bypass capacitor to prevent power disturbance. For the SN54SC1G175-SEP, a  $0.1\mu\text{F}$  bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of  $0.1\mu\text{F}$  and  $1\mu\text{F}$  are commonly used in parallel.

### 8.4 Layout

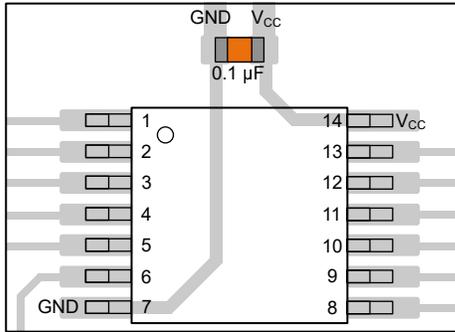
#### 8.4.1 Layout Guidelines

- Bypass capacitor placement
  - Place near the positive supply terminal of the device
  - Provide an electrically short ground return path
  - Use wide traces to minimize impedance
  - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
  - 8mil to 12mil trace width
  - Lengths less than 12cm to minimize transmission line effects
  - Avoid  $90^\circ$  corners for signal traces
  - Use an unbroken ground plane below signal traces
  - Flood fill areas around signal traces with ground
  - Parallel traces must be separated by at least 3x dielectric thickness
  - For traces longer than 12cm
    - Use impedance controlled traces
    - Source-terminate using a series damping resistor near the output
    - Avoid branches; buffer each signal that must branch separately

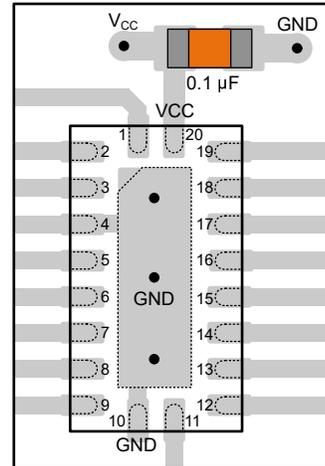
#### 8.4.2 Layout Example



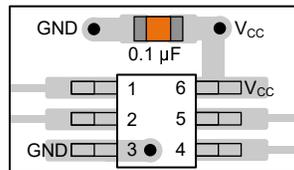
**Figure 8-3. Example Trace Corners for Improved Signal Integrity**



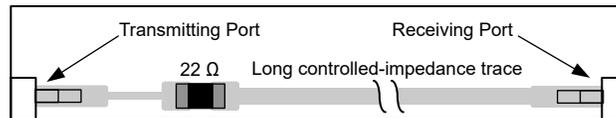
**Figure 8-4. Example Bypass Capacitor Placement for TSSOP and Similar Packages**



**Figure 8-5. Example Bypass Capacitor Placement for WQFN and Similar Packages**



**Figure 8-6. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages**



**Figure 8-7. Example Damping Resistor Placement for Improved Signal Integrity**

## 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and  \$C\_{pd}\$  Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 9.4 Trademarks

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### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
February 2026	*	Initial Release

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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Last updated 10/2025